

## CIR-S3SUSPM1808G

DDR3 SO-DIMM 1866MHz 8GB

### Description

The CIR-S3SUSPM1808G is 1024M words X 64 bits, 2 ranks. Unbuffered Small Outline Dual In-Line Memory Module (SO-DIMM). DDR3 SDRAMs in Fine Ball Grid Array (FBGA) packages on a 204pin glass-epoxy substrate. Provide a high performance 8 byte interface in 67.60mm width form factor of industry standard. It is suitable for easy interchange and addition.

### Specifications

Density	8GB
Pin Count	204pin
Type	Unbuffered
Dimensions	67.6mm x 30.0mm
ECC	Non-ECC
Component Config	512M x 8 bit
Data Rate	1866 MHz
CAS Latency	13
Voltage	1.5V / 1.35V
PCB Layers	8
Operating Temp.(TCASE)	0°C~+85°C
Module Ranks	Dual Rank

### Features

- Data rate:1866MHz
- RoHS compliant products.
- 204pin,Small outline dual in-line memory module(SO-DIMM)
- Power supply: VDD= 1.5V (1.425V to 1.575V) & VDD= 1.35V (1.283V to 1.45V)
- Programmable CAS Latency(CL):6,7,8,9,10,11,12,13 support
- Fully differential clock inputs (CK, /CK) operation
- Differential Data Strobe (DQS, /DQS)
- Serial presence detect with EEPROM
- 8 independent internal bank
- 8K refresh cycles /64ms
- On Die Termination supported
- Asynchronous RESET pin supported
- ZQ calibration supported
- Programmable Additive Latency(Posted CAS) : 0, CL - 2, or CL - 1 clock
- Bi-directional Differential Data Strobe
- Burst Length: 4, 8
- 8 bit pre-fetch
- Average Refresh Period 7.8us at  $0^{\circ}\text{C} \leq \text{TC} \leq 85^{\circ}\text{C}$   
3.9us at  $85^{\circ}\text{C} < \text{TC} \leq 95^{\circ}\text{C}$

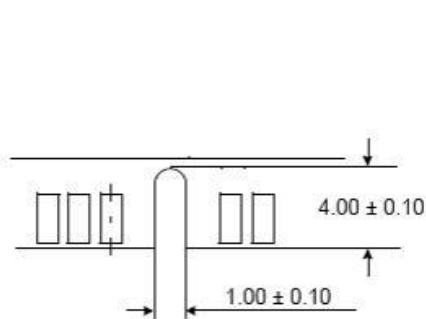
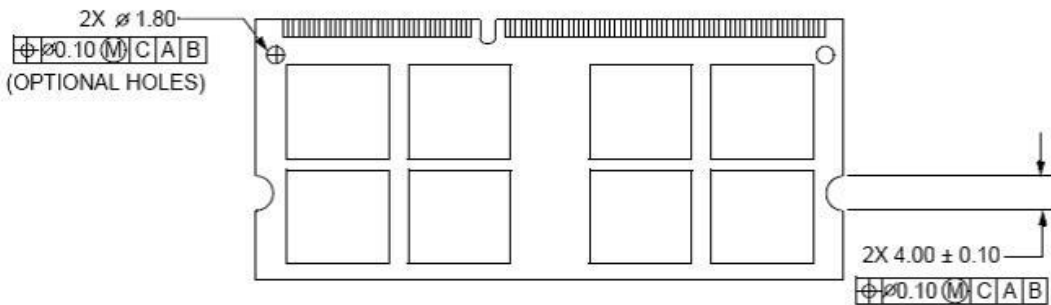
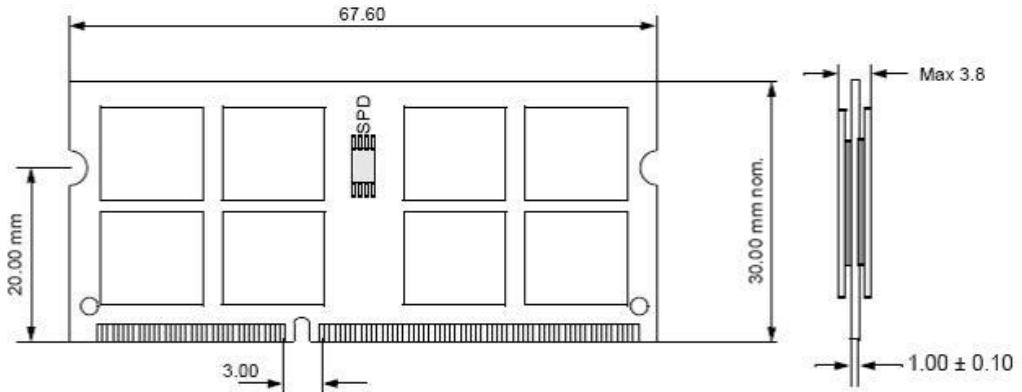


**Speed Grade**

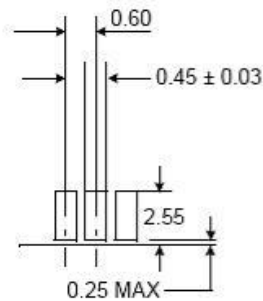
Frequency Grade	Data Transfer Rate	CAS Latency Support								CL-tRCD-tRP
		CL6	CL7	CL8	CL9	CL10	CL11	CL12	CL13	
DDR3-1866	PC3-14900	800	1066	1066	1333	1333	1600	1600	1866	13-13-13

**Package Dimensions**

Unit: mm



**Detail A**



**Detail B**

Tolerances :  $\pm 0.15$ mm unless otherwise specified